

Appl. No. 10/733,984  
Examiner: MONDT, JOHANNES P, Art Unit 2826  
In response to the Office Action dated July 13, 2005

Date: September 27, 2005  
Attorney Docket No. 10113311

#### AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 3, line 27 with the following amended paragraph:

– The present invention also provides a structure for a bit line contact hole. The structure comprises a substrate, a transistor, an inner landing pad, a passivation layer, a first insulating layer, a second insulating layer, a contact plug, and an interconnected landing pad. The transistor comprising a gate layer covered by a first insulating layer and a doped region is disposed on the substrate. The inner landing pad comprising a polysilicon layer is disposed on the doped region and parts of the transistor. The passivation layer is disposed on the inner landing pad, the transistor, and the substrate. The second insulating layer, having a flat surface, is disposed on the passivation layer. The contact plug contacting and electrically connecting with the inner landing pad is disposed on the second insulating layer and the passivation layer. The interconnected landing pad is disposed on the contact plug.